℃		

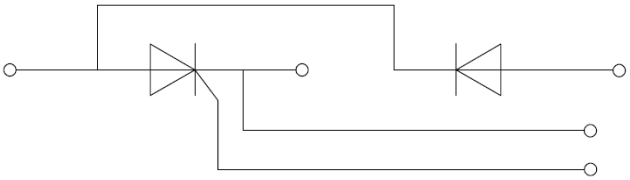

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FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

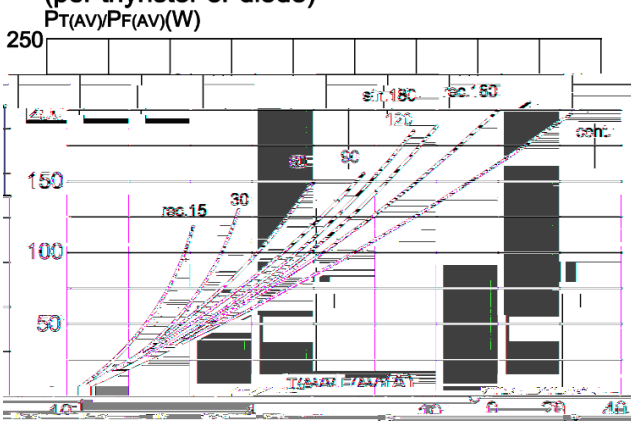


FIG.2: Maximum transient thermal impedance junction to case(per thyristor or diode)

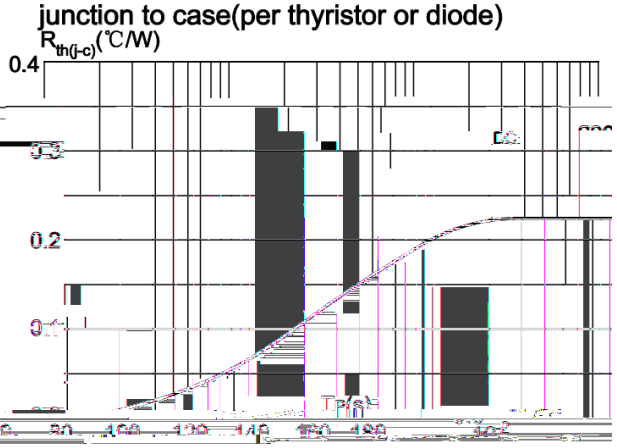


FIG.3: Forward characteristics (per thyristor or diode)

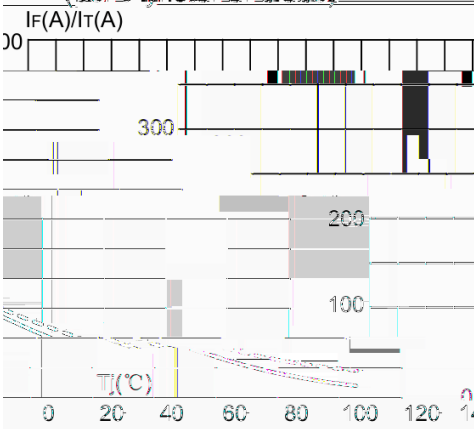
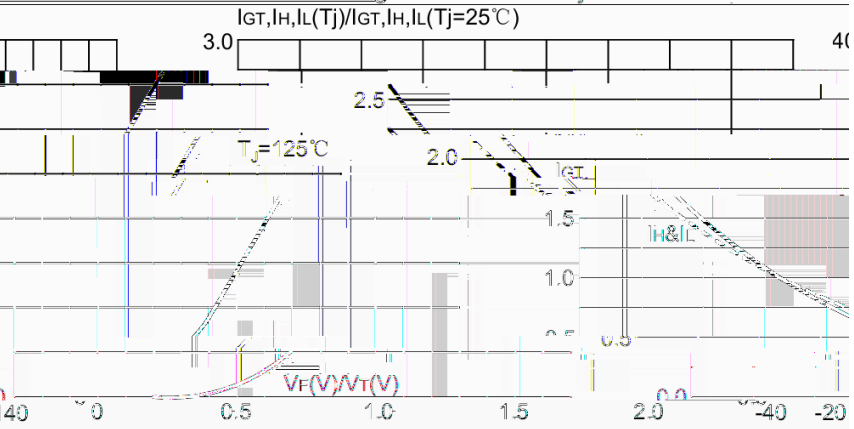


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature



ature

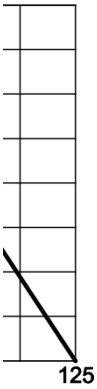


FIG.5 Gate trigger characteristics

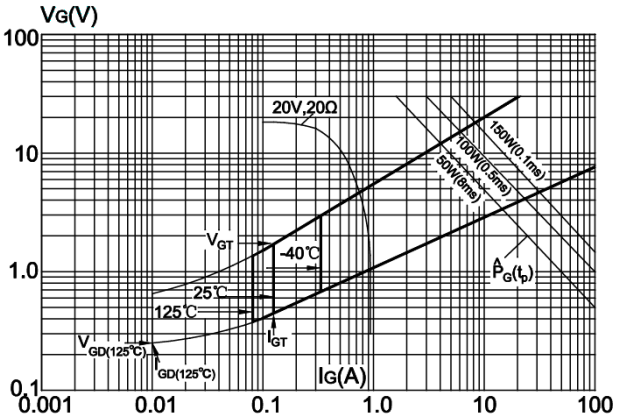
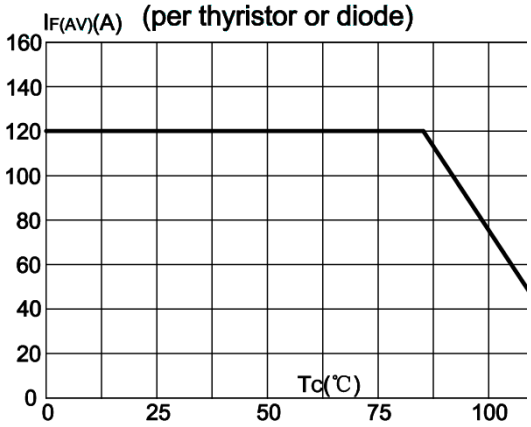
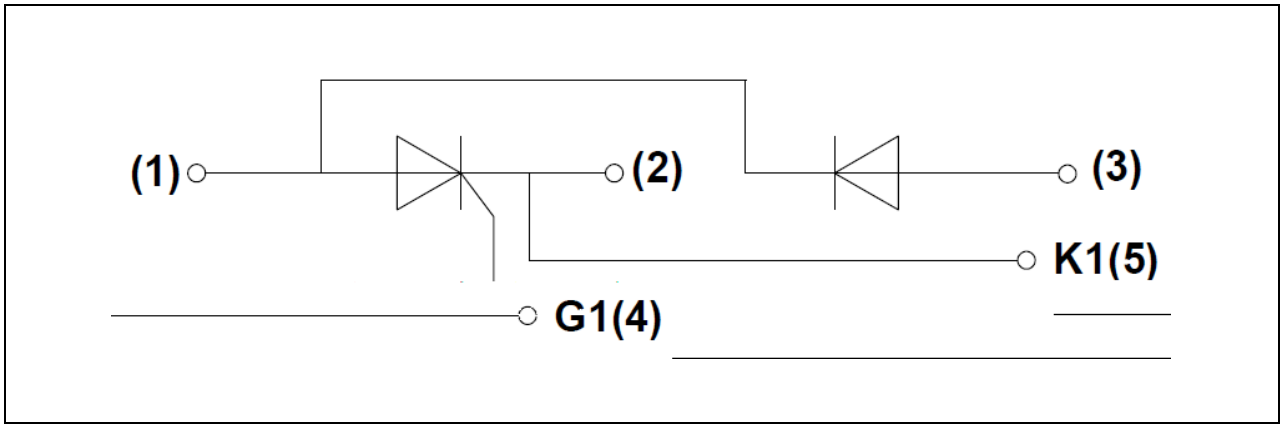
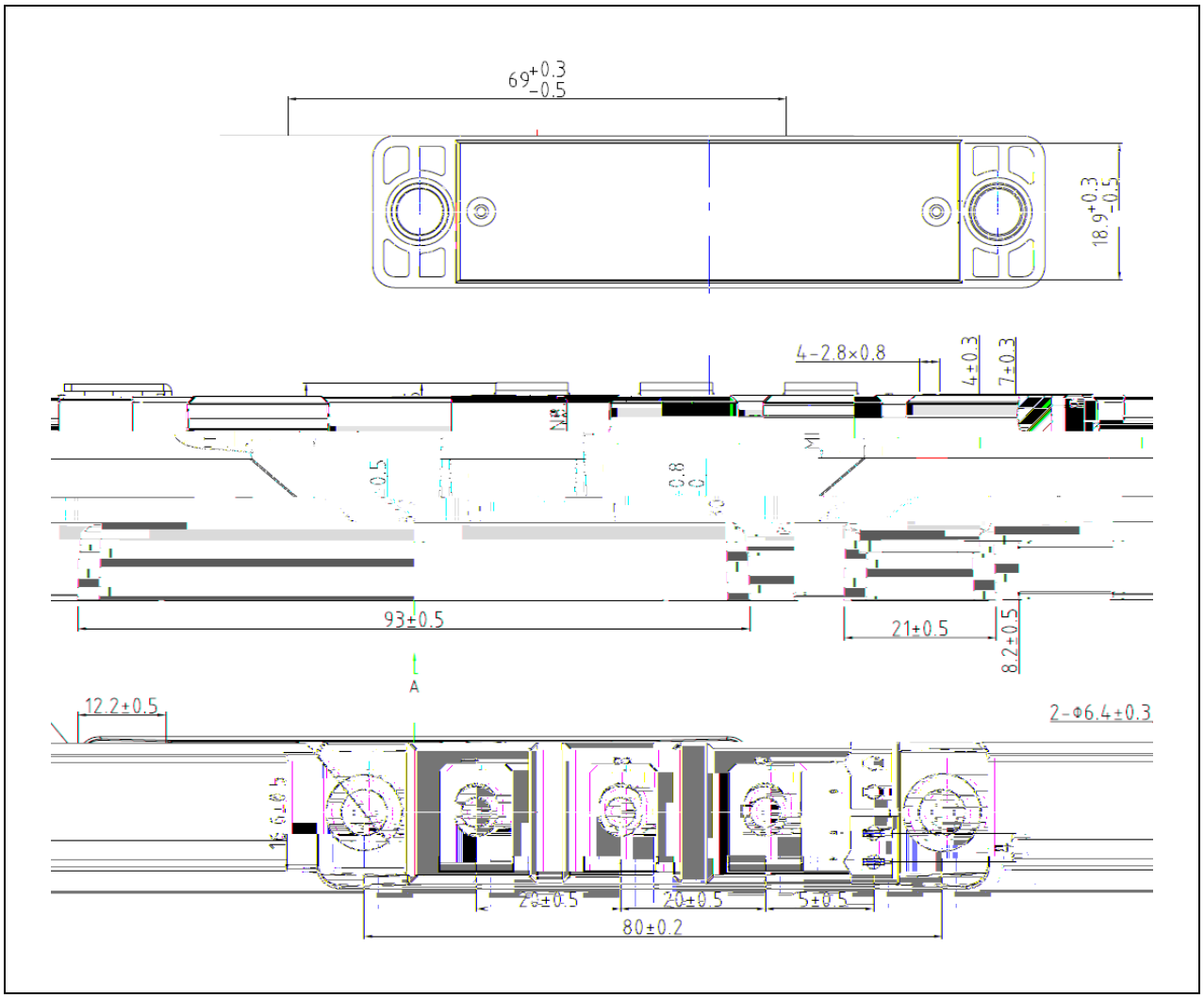


FIG.6: Forward current vs. case temper (per thyristor or diode)




(1)
(2)
(3)
K1(5)
G1(4)


69+0.3 -0.5
18.9+0.3 -0.5
4-2.8×0.8
4±0.3
7±0.3
93±0.5
21±0.5
8.2±0.5
A
12.2±0.5
2-Φ6.4±0.3
20±0.5
20±0.5
5±0.5
80±0.2